

# UNISONIC TECHNOLOGIES CO., LTD

7N20Z **Power MOSFET** 

# **7A, 200V N-CHANNEL POWER MOSFET**

#### **DESCRIPTION**

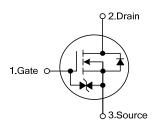
The UTC 7N20Z is an N-Channel enhancement mode power MOSFET providing customers with excellent switching performance and minimum on-state resistance. This device can also withstand high energy pulse in the avalanche and the commutation mode.

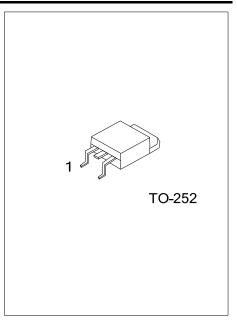
The UTC 7N20Z is generally applied in low voltage applications, such as DC motor controls, audio amplifiers and high efficiency switching DC/DC converters.

# **FEATURES**

- \* Low Gate Charge: 5.8nC (TYP.)
- \* Low C<sub>RSS:</sub> 10 pF (TYP.)
- \*  $R_{DS(ON)} = 0.58\Omega @V_{GS} = 10 V$
- \* Fast Switching
- \* Improved dv/dt Capability

#### **SYMBOL**

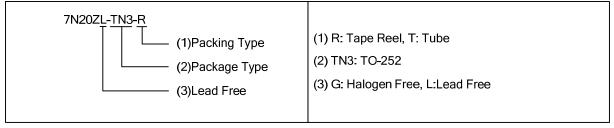




# **ORDERING INFORMATION**

Ordering Number		Daalaaaa	Pin Assignment			Dealing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
7N20ZL-TN3-R	7N20ZG-TN3-R	TO-252	G	D	S	Tape Reel	
7N20ZL-TN3-T	7N20ZG-TN3-T	TO-252	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



# ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub> =25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain -Source Voltage	$V_{ extsf{DSS}}$	200	٧	
Gate-Source Voltage	$V_{GSS}$	±25	V	
Continuous Drain Current T <sub>C</sub> =25°C	I <sub>D</sub>	7	Α	
Pulsed Drain Current (Note 2)	I <sub>DM</sub>	28	Α	
Single Pulsed Avalanche Energy (Note 3)	E <sub>AS</sub>	130	mJ	
Power Dissipation	$P_D$	2.5	W	
Operating Junction Temperature	T <sub>J</sub>	150	°C	
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C	

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature
- 3. L =26mH,  $I_{AS}$  =7A,  $V_{DD}$  =25V,  $R_G$  =25 $\Omega$  Starting  $T_J$  =25 $^{\circ}$ C

# ■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	50	°C/W

Note: When mounted on the minimum pad size recommended (PCB Mount)

# ■ **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> =25°C, unless otherwise specified)

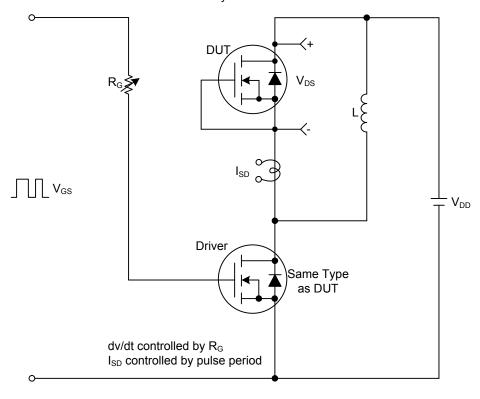
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250 \mu A$	200			V	
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =200V, V <sub>GS</sub> =0V			1	μΑ	
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 25V$ , $V_{DS} = 0V$			±10	μΑ	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$			4.0	V	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	$V_{GS} = 10V, I_D = 3.5A$		0.58	0.69	Ω	
DYNAMIC PARAMETERS							
Input Capacitance	C <sub>ISS</sub>			190	250	pF	
Output Capacitance	Coss	$V_{DS}$ =25V, $V_{GS}$ =0V, f=1.0MHz		60	75	pF	
Reverse Transfer Capacitance	$C_{RSS}$			10	13	pF	
SWITCHING PARAMETERS							
Total Gate Charge	$Q_G$	\/ -40\/ \/ -400\/   -74		5.8	7.5	nC	
Gate Source Charge	$Q_GS$	V <sub>GS</sub> =10V, V <sub>DS</sub> =100V, I <sub>D</sub> =7A		1.4		nC	
Gate Drain Charge	$Q_GD$	(Note 1,2)		2.5		nC	
Turn-ON Delay Time	t <sub>D(ON)</sub>			7	25	ns	
Turn-ON Rise Time	$t_R$	$V_{DD}$ =50V, $I_{D}$ =7A, $R_{G}$ =25 $\Omega$		24	60	ns	
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	(Note 1,2)		13	35	ns	
Turn-OFF Fall-Time	$t_{F}$			19	50	ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode	ı				7	Α	
Forward Current	I <sub>S</sub>				1	A	
Maximum Pulsed Drain-Source Diode	Levi				28	Α	
Forward Current	I <sub>SM</sub>				20	A	
Drain-Source Diode Forward Voltage	$V_{SD}$	$I_S = 7A$ , $V_{GS} = 0V$			1.5	V	

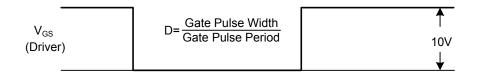
Notes: 1. Pulse Test : Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$ 

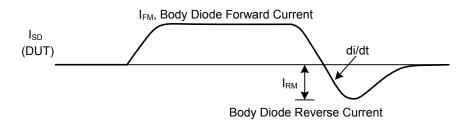
2. Essentially independent of operating temperature

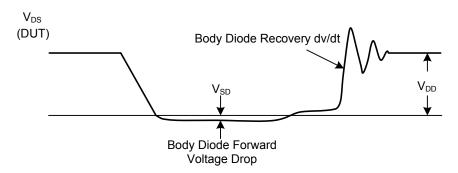
# **■ TEST CIRCUITS AND WAVEFORMS**

Peak Diode Recovery dv/dt Test Circuit & Waveforms

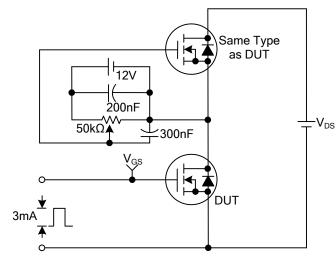








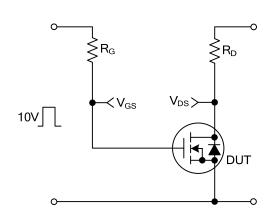
# ■ TEST CIRCUITS AND WAVEFORMS (Cont.)



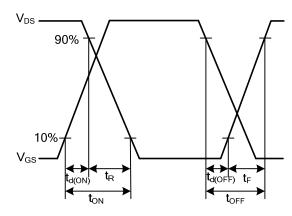
 $V_{GS}$   $Q_{G}$   $Q_{G}$   $Q_{GD}$   $Q_{GD}$   $Q_{GD}$   $Q_{GD}$ 

**Gate Charge Test Circuit** 

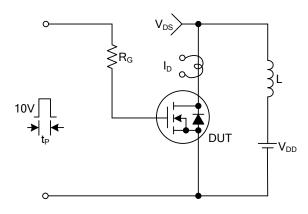
**Gate Charge Waveforms** 



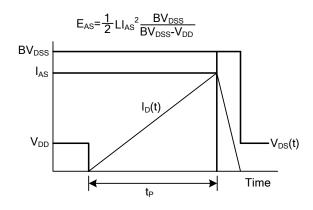
**Resistive Switching Test Circuit** 



**Resistive Switching Waveforms** 

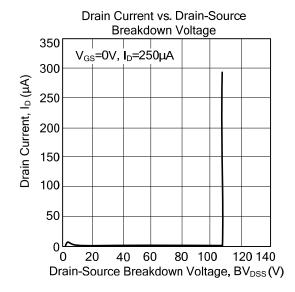


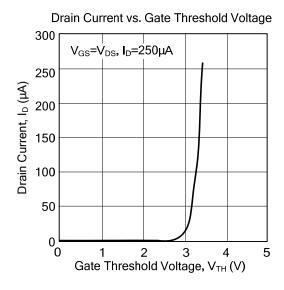
**Unclamped Inductive Switching Test Circuit** 

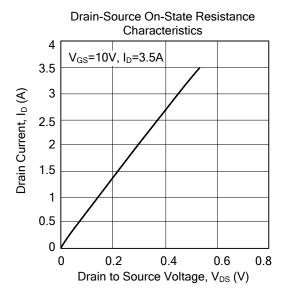


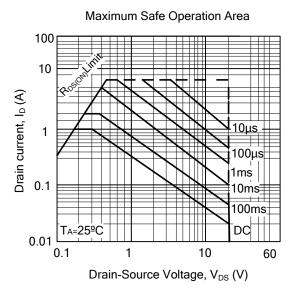
**Unclamped Inductive Switching Waveforms** 

# ■ TYPICAL CHARACTERISTICS









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